forming source and drain regions connected to the channel region in a semiconductor film that is formed on a surface of an insulating substrate; and

forming a recombination center by introducing an impurity into the channel region so that a distance between the recombination center and the drain region is shorter than a distance between the recombination center and the source region.

2. (Twice Amended) The method of manufacturing a thin-film transistor according to Claim 1, wherein said impurity being at least one kind selected from the group including inert gases, metals, Group III elements, Group IV elements and Group V elements.

7. (Three Times Amended) The method of manufacturing a thin-film transistor according to Claim 3, wherein an average projected range of the impurity in said process of introducing an impurity being from a center in a direction of thickness of said channel region to an interface between the channel region and the gate insulating film.

8. (Three Times Amended) The method of manufacturing a thin-film transistor according to Claim 3, wherein an average projected range of the impurity in said process of introducing an impurity being from a center in a direction of thickness of said channel region to an interface between the channel region and a layer located on said substrate side.

9. (Twice Amended) The method of manufacturing a thin-film transistor according to Claim 1, wherein a process of introducing said impurity to said channel region being carried out by impurity diffusion from an impurity diffusion source arranged at a lower layer side of said channel region.

10. (Twice Amended) The method of manufacturing a thin-film transistor according to Claim 9, wherein said impurity diffusion being carried out in a crystallization process on a semiconductor film so as to form said channel region.

11. (Three Times Amended) The method of manufacturing a thin-film transistor according to Claim 4, wherein said crystallization process being laser annealing on a semiconductor film so as to form said channel region.

12. (Three Times Amended) The method of manufacturing a thin-film transistor according to Claim 1, wherein each process carried out after introducing said impurities to said channel region being carried out at a temperature below 400°C.

13. (Three Times Amended) The method of manufacturing a thin-film transistor according Claim 1, wherein each process carried out after introducing said impurities to said channel region being carried out at a temperature below 300°C.

Please add new claims 15-24 as follows:

--15. The method of claim 1, wherein the distance from the recombination center to the drain region and the distance from the recombination center to the source region are in the range of 1/10 to 1/3 of the channel length.--

--16. A thin-film transistor, comprising:

a channel region facing a gate electrode through a gate insulating film;

source and drain regions connected to the channel region in a semiconductor film in contact with a surface of an insulating substrate; and

a recombination center in contact with the channel region so that a distance between the recombination center and the drain region is shorter than a distance between the recombination center and the source region.--

--17. The thin-film transistor according to Claim 16, wherein said recombination center is formed by introducing an impurity into said channel region, said impurity being at least one kind selected from the group including inert gases, metals, Group II elements, Group IV and Group V elements.--

--18. The thin-film transistor according to Claim 16, wherein said recombination center is formed by introducing an impurity into said channel region by injecting the impurity from a surface side of said channel.--

--19. The thin-film transistor according to Claim 18, wherein a process of introducing said impurity into said channel region is carried out, after a crystallization process on a semiconductor film so as to form said channel region, by injecting the impurity from a surface side of said channel region.--

--20. The thin-film transistor according to Claim 18, wherein a process of introducing said impurity into said channel region is carried out, after a crystallization process on a semiconductor film so as to form said channel region, by injecting the impurity from a surface side of said channel region before a process of forming said gate electrode on a surface side of the channel region.--

--21. The thin-film transistor according to Claim 18, wherein a process of introducing said impurity into said channel region is carried out, after said gate insulating film and said gate electrode are sequentially formed on a surface side of said channel region, by injecting the impurity from a surface side of said gate electrode before an interlayer insulating film is formed on a surface side of the gate electrode.--

--22. The thin-film transistor according to Claim 18, wherein an average projected range of the impurity in said process of introducing an impurity being from a center in a direction of thickness of said channel region to an interface between the channel region and the gate insulating film.--

--23. The thin-film transistor according to Claim 18, wherein an average projected range of the impurity in said process of introducing an impurity being from a center in a direction of thickness of said channel region to an interface between the channel region and a layer located on said substrate side.--